

AP1003-40M9

2.5 Gb/s 1490nm Avalanche Photodiode



AP1003-40M9 is a 2.5 Gb/s germanium on silicon avalanche photodiode for PON applications.

Features

- Top-illuminated device for ease of assembly
- Both P and N pads on top side
- Low breakdown voltage of 30 V
- Low capacitance of 0.25 pF
- Responds to an 800nm - 1600nm wavelength range
- AR coating optimized for 1490nm applications
- Typical responsivity at 1490 nm is 0.85 A/W @ M=1
- Optical illumination aperture 40 μ m

Applications

- PON